Quad 3-State Noninverting Buffer with LSTTL Compatible Inputs

High-Performance Silicon-Gate CMOS

The MC74HCT125A is identical in pinout to the LS125. The device inputs are compatible with standard CMOS and LSTTL outputs.

The MC74HCT125A noninverting buffer is designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. The devices have four separate output enables that are active-low.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the JEDEC Standard No. 7A Requirements
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb–Free Devices

PIN ASSIGNMENT

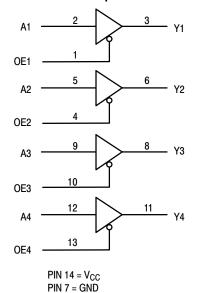
0E1 [1 ●	14	v _{cc}
A1 [2	13	0E4
Y1 [3	12] A4
OE2 [4	11] Y4
A2 [5	10	0E3
Y2 [6	9] A3
GND [7	8] Y3
			J

FUNCTION TABLE

HCT125A					
Inputs Output					
Α	OE	Υ			
Н	L	Н			
L	L	L			
Χ	Н	Z			

LOGIC DIAGRAM

Active-Low Output Enables





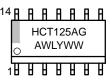
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MARKING DIAGRAMS



SOIC-14 D SUFFIX CASE 751A





TSSOP-14 DT SUFFIX CASE 948G



A = Assembly Location

L, WL = Wafer Lot Y, YY = Year

W, WW = Work Week
G = Pb-Free Package
• Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
l _{in}	DC Input Current, per Pin	± 20	mA
I _{out}	DC Output Current, per Pin	± 35	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 75	mA
P _D	Power Dissipation in Still Air SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — SOIC Package: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)		0	V _{CC}	V
T _A	Operating Temperature, All Package Types		- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	$V_{CC} = 2.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V _{CC} V	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{\text{out}} = V_{\text{CC}} - 0.1 \text{ V}$ $ I_{\text{out}} \le 20 \mu\text{A}$	4.5 to 5.5	2.0	2.0	2.0	V
V _{IL}	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	4.5 to 5.5	0.8	0.8	0.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \le 20 \mu A$	4.5 5.5 4.5	4.4 5.4 3.98	4.4 5.4	4.4 5.4 3.7	V
V _{OL}	Maximum Low–Level Output Voltage	$\begin{aligned} &V_{in} = V_{IH} & & I_{out} \leq 6.0 \text{ mA} \\ &V_{in} = V_{IL} & & \\ & I_{out} \leq 20 \mu\text{A} \end{aligned}$	4.5 5.5	0.1 0.1	3.84 0.1 0.1	0.1 0.1	V
l _{in}	Maximum Input Leakage Current	$V_{in} = V_{IL}$ $ I_{out} \le 6.0 \text{ mA}$ $V_{in} = V_{CC} \text{ or GND}$	4.5 5.5	0.26 ± 0.1	0.33 ± 1.0	0.4 ± 1.0	μΑ
I _{OZ}	Maximum Three–State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND	5.5	± 0.5	± 5.0	± 10	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	5.5	4.0	40	160	μΑ

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6.0 ns, V_{CC} = 5.0 V \pm 10%)

			Guaranteed Limit			
Symbol	Parameter	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3)	5.0	18	23	27	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4)	5.0	24	30	36	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to Y (Figures 2 and 4)	5.0	18	23	27	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	5.0	12	15	18	ns
C _{in}	Maximum Input Capacitance	-	10	10	10	pF
C _{out}	Maximum 3-State Output Capacitance (Output in High-Impedance State)	_	15	15	15	pF
			Typical @ 25°C, V _{CC} = 5.0 V			
_			1	00		_

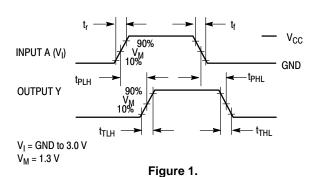
ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HCT125ADG		55 Units / Rail
MC74HCT125ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
NLV74HCT125ADR2G*	(1 11)	2500 / Tape & Reel
MC74HCT125ADTG		96 Units / Rail
MC74HCT125ADTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
NLVHCT125ADTR2G*	, , ,	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

SWITCHING WAVEFORMS



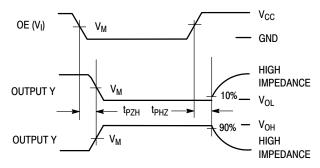
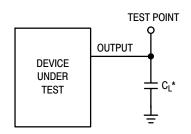
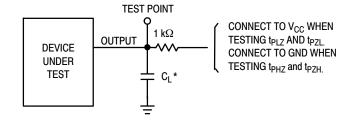


Figure 2.



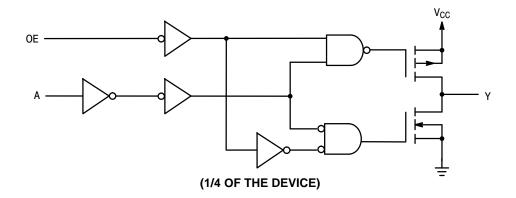


*Includes all probe and jig capacitance

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Figure 3. Test Circuit

Figure 4. Test Circuit



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